

# MICRO ELECTRONICS

查询MPS6516供应信息

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PNP  
SILICON PLANAR  
EPITAXIAL TRANSISTORS

MPS6516 thru' MPS6519 are PNP silicon planar epitaxial transistors designed for general purpose amplifier applications and for complementary circuitry.

CASE TO-92A



### ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage  
Collector-Base Voltage  
Emitter-Base Voltage  
Collector Current  
Total Power Dissipation @  $T_A=25^\circ\text{C}$   
@  $T_C=25^\circ\text{C}$   
Operating Junction & Storage Temperature

	MPS6516/7/8	MPS6519
V <sub>CEO</sub>	40V	25V
V <sub>CB0</sub>	40V	25V
V <sub>EB0</sub>	4V	4V
I <sub>C</sub>	100mA	100mA
P <sub>tot</sub>	350mW	350mW
	1W	1W
T <sub>j</sub> , T <sub>stg</sub>	-55 to +150°C	

### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	40		25	V	I <sub>C</sub> =0.5mA I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EB0</sub>	4			V	I <sub>E</sub> =10μA I <sub>C</sub> =0
Collector Cutoff Current	IC <sub>B0</sub>			50	nA	V <sub>CB</sub> =30V I <sub>E</sub> =0
				50	nA	V <sub>CB</sub> =20V I <sub>E</sub> =0
Collector Cutoff Current	IC <sub>B0</sub>			1	μA	T <sub>A</sub> =60°C V <sub>CB</sub> =30V I <sub>E</sub> =0
				1	μA	V <sub>CB</sub> =20V I <sub>E</sub> =0
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>			0.5	V	I <sub>C</sub> =50mA I <sub>B</sub> =5mA
D.C. Current Gain	H <sub>FE</sub>	50		100		I <sub>C</sub> =2mA V <sub>CE</sub> =10V
		90		180		
		150		300		
		250		500		
D.C. Current Gain	H <sub>FE</sub> *	30				I <sub>C</sub> =100mA V <sub>CE</sub> =10V
		60				
		90				
		150				
Current Gain-Bandwidth Product	f <sub>T</sub>		150		MHz	I <sub>C</sub> =2mA V <sub>CE</sub> =10V
			250		MHz	I <sub>C</sub> =10mA V <sub>CE</sub> =10V

\* Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%

P.T.O.

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ELECTRICAL CHARACTERISTICS ( $T_A=25^{\circ}\text{C}$  unless otherwise)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Output Capacitance	Cob			4	pF	V <sub>CB</sub> =10V I <sub>E</sub> =0 f=100kHz
Noise Figure	NF		2		dB	I <sub>C</sub> =10 $\mu$ A V <sub>CE</sub> =5V R <sub>S</sub> =10K $\Omega$ Power Bandwidth =15.7KHz, 3dB points @ 10Hz & 10kHz

11/20/27M  
1/2 98-98